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(12) **United States Design Patent**  
**Iwafuchi et al.**

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(54) **SEMICONDUCTOR ELEMENT**

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(51) **LOC (7) Cl.** ..... **13-03**

(52) **U.S. Cl.** ..... **D13/182**

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D14/212, 233; 257/10, 77, 103, 190, 622,  
627; 216/11; 313/309, 310, 311, 327; 428/332;  
438/20; 445/24, 50, 51, 58

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(57) **CLAIM**

The ornamental design for a semiconductor element, as shown and described.

**DESCRIPTION**

FIG. 1 is a top, left, front perspective view of a semiconductor element showing our new design;

FIG. 2 is a bottom, left, front perspective view thereof;

FIG. 3 is a front elevational view thereof; and

FIG. 4 is a rear elevational view thereof.

FIG. 5 is a left side elevational view thereof;

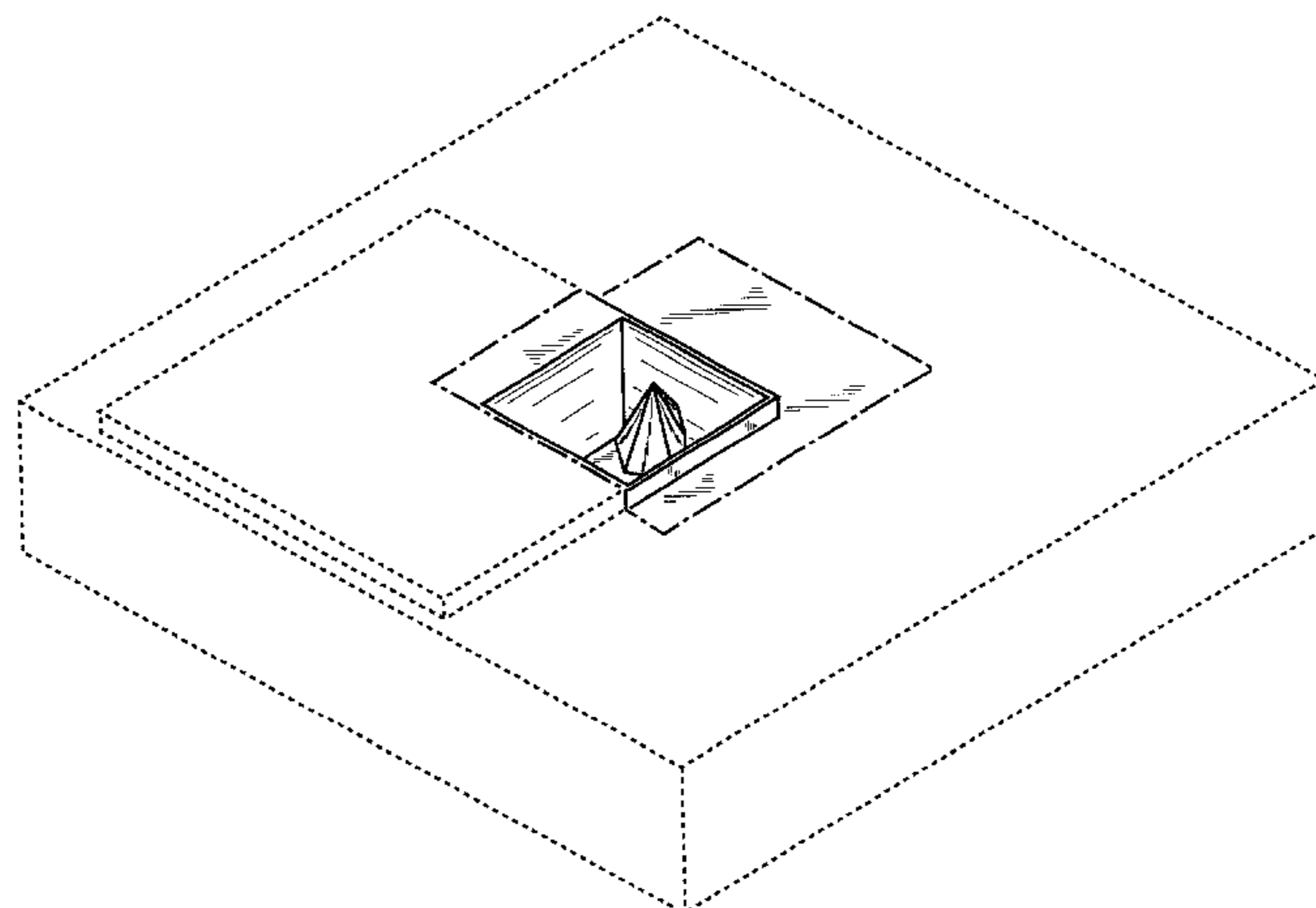
FIG. 6 is a right side elevational view thereof;

FIG. 7 is a top plan view thereof; and,

FIG. 8 is a bottom plan view thereof.

The portions in even broken lines are for illustrative purposes only and form no part of the claimed design. The portions in dot-dash broken lines define, but are not included in, the boundaries of the claimed design.

**1 Claim, 5 Drawing Sheets**



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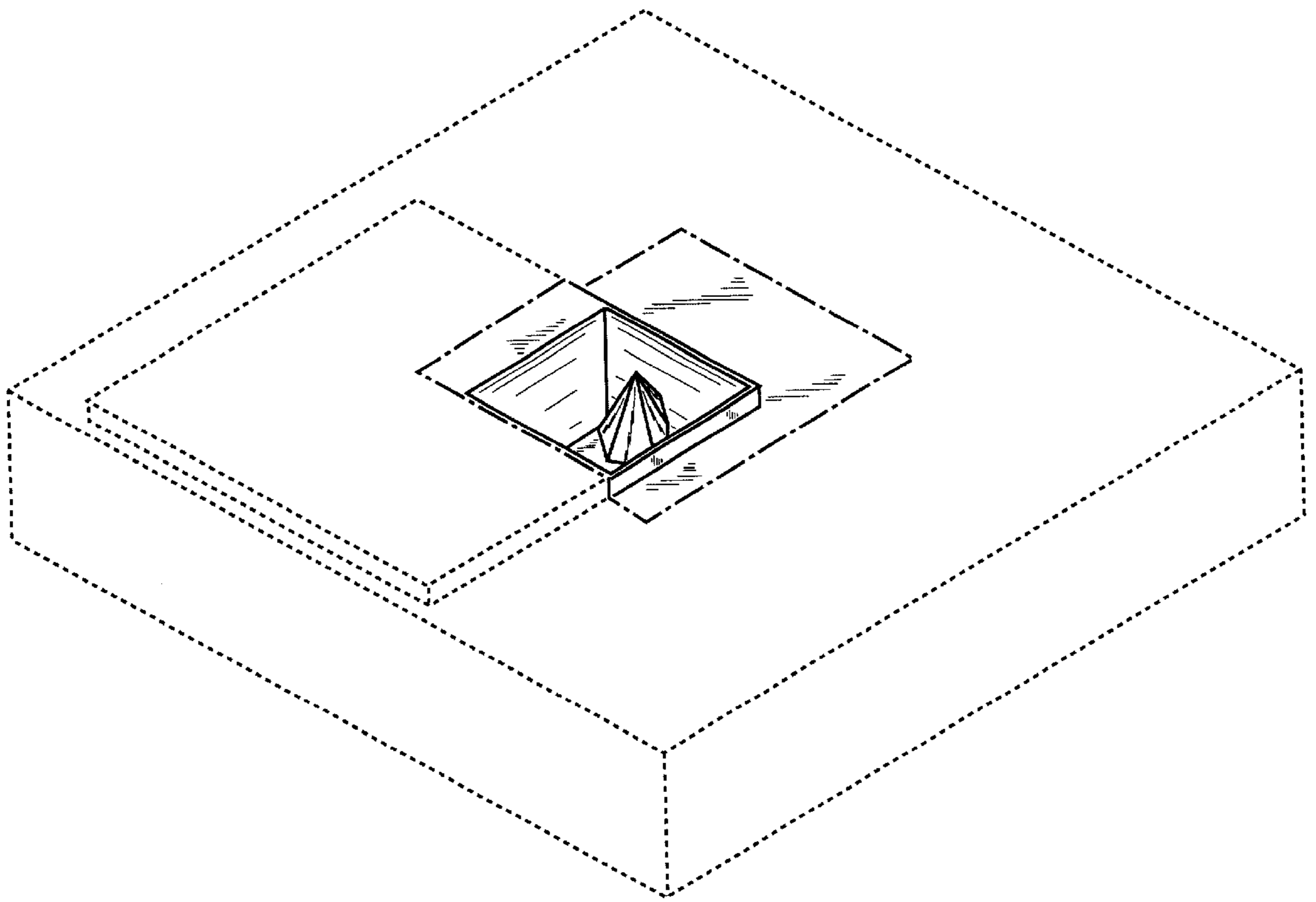


Fig. 1

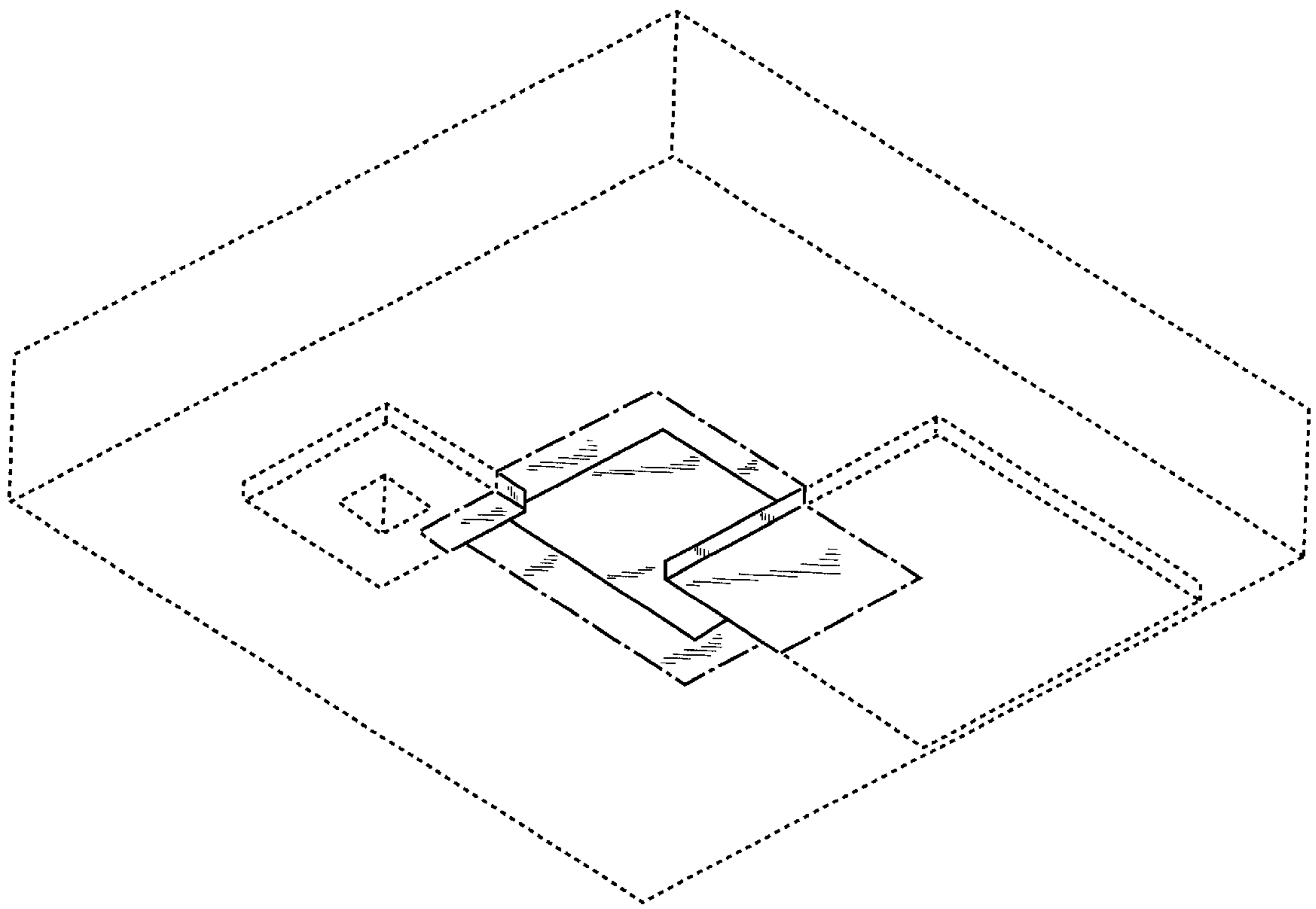


Fig. 2

Fig. 3

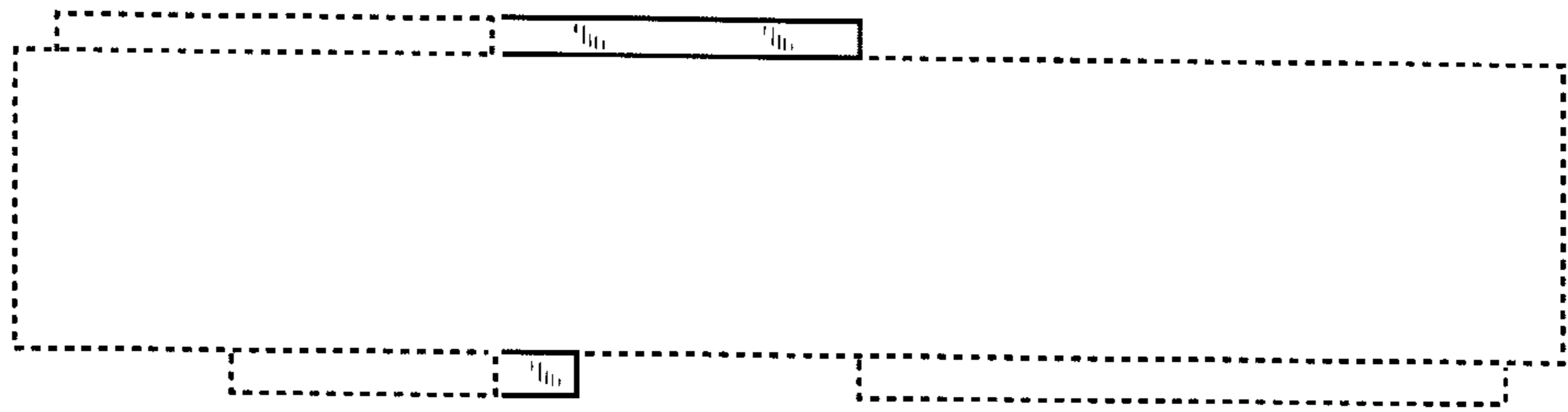


Fig. 4

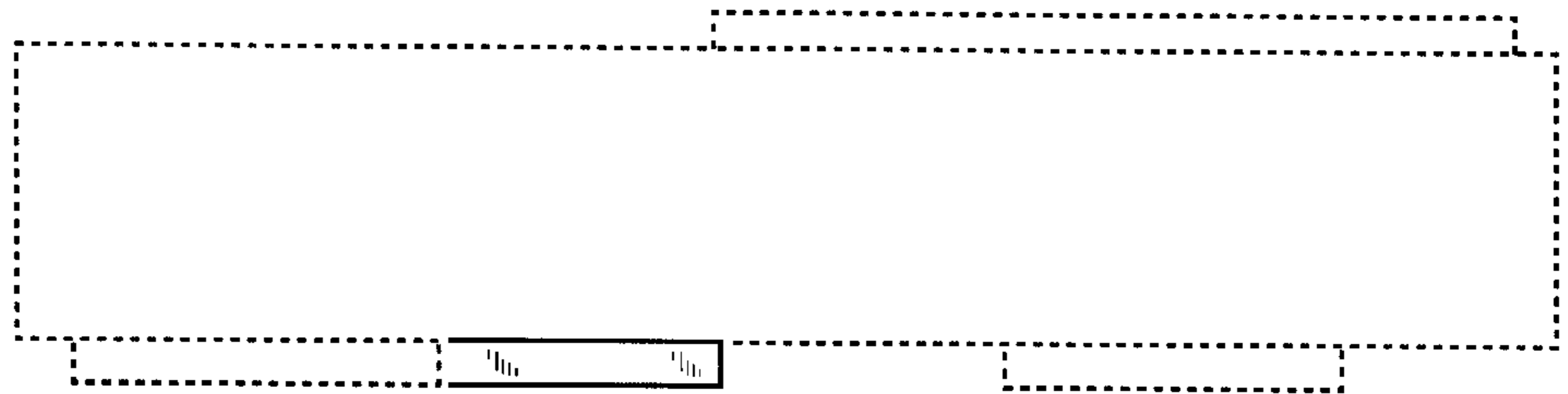


Fig. 5

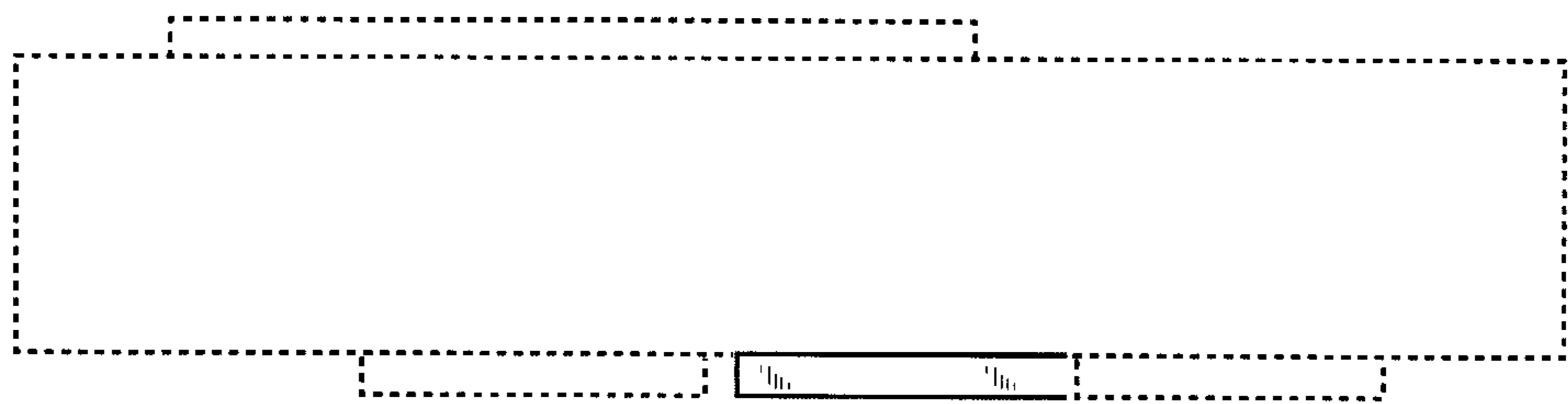
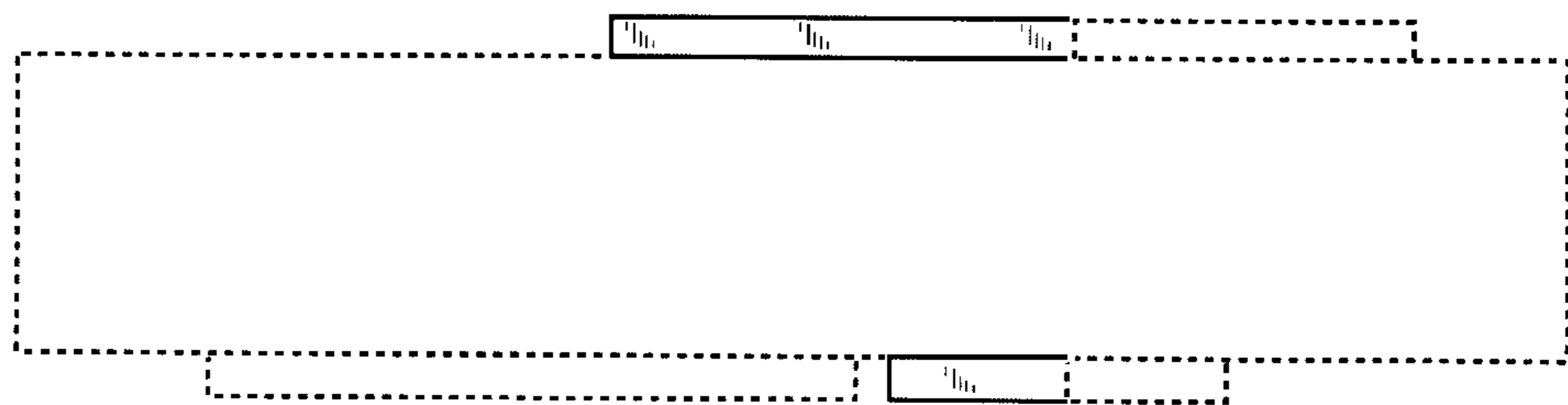


Fig. 6



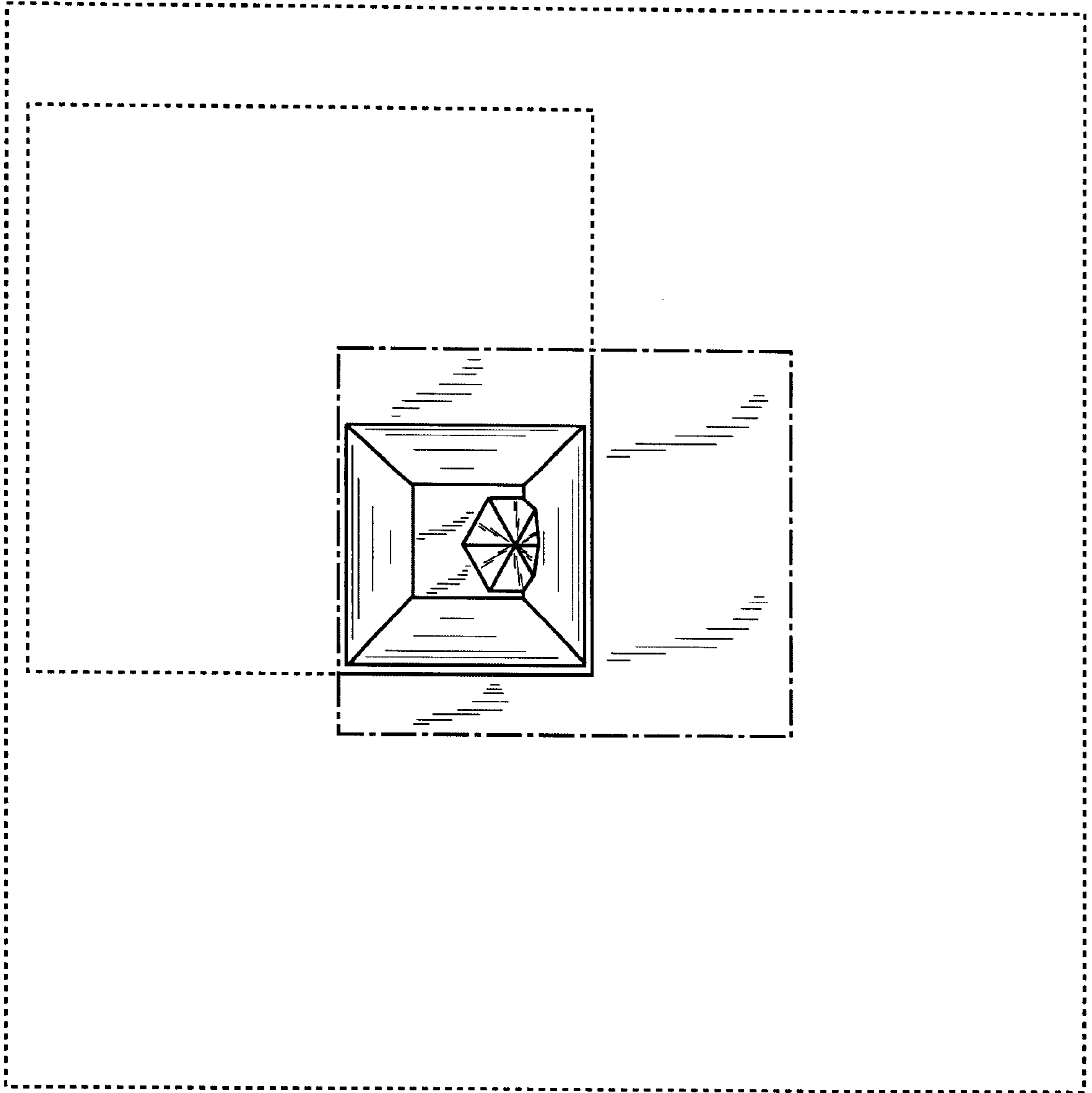


Fig. 7

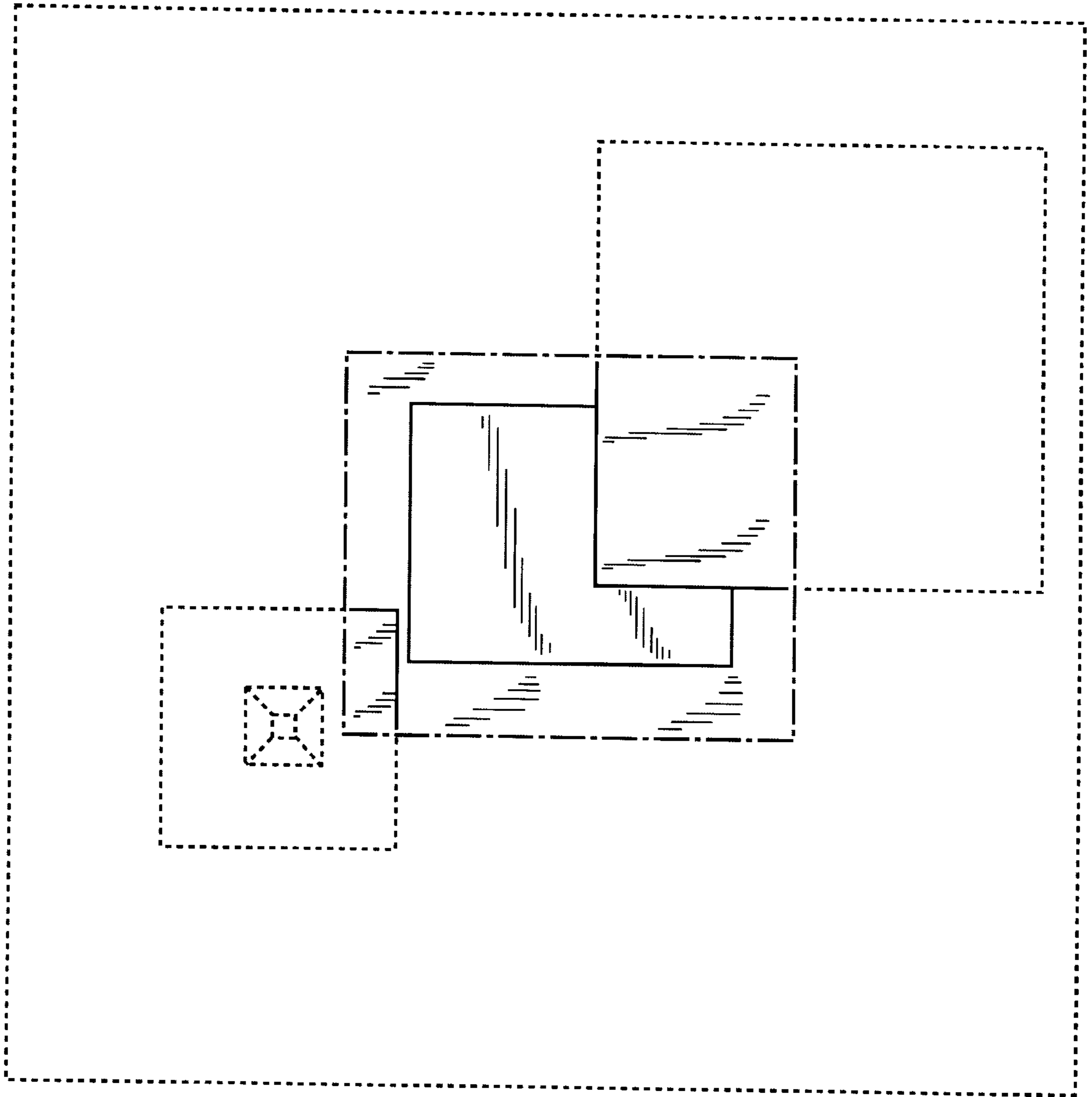


Fig. 8